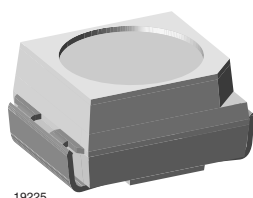


Standard SMD LED PLCC-2



19225

DESCRIPTION

This device has been redesigned in 1998 replacing SiC by GaN technology to meet the increasing demand for high efficiency blue LEDs.

The package of the TLMB310. is the PLCC-2 (equivalent to a size B tantalum capacitor).

It consists of a lead frame which is embedded in a white thermoplast. All LEDs are categorized in luminous intensity groups. That allows users to assemble LEDs with uniform appearance.

PRODUCT GROUP AND PACKAGE DATA

- Product group: LED
- Package: SMD PLCC-2
- Product series: standard
- Angle of half intensity: $\pm 60^\circ$

FEATURES

- GaN on SiC technology
- EIA and ICE standard package
- Compatible with infrared, vapor phase and wave solder processes according to CECC
- Available in 8 mm tape
- Non-diffused lens: excellent for coupling to light pipes and backlighting
- Luminous intensity ratio in one packaging unit $I_{Vmax}/I_{Vmin} \leq 1.6$
- ESD class 1
- Lead (Pb)-free device



APPLICATIONS

- Automotive: backlighting in dashboards and switches
- Telecommunication: indicator and backlighting in telephone and fax
- Indicator and backlight for audio and video equipment
- Indicator and backlight in office equipment
- Flat backlight for LCDs, switches and symbols
- General use

PARTS TABLE

| PART | COLOR, LUMINOUS INTENSITY | TECHNOLOGY |
|----------|--|------------|
| TLMB3100 | Blue, $I_V > 4.0$ mcd | GaN on SiC |
| TLMB3101 | Blue, $I_V = (4.0 \text{ to } 12.5)$ mcd | GaN on SiC |
| TLMB3104 | Blue, $I_V = (5.0 \text{ to } 12.5)$ mcd | GaN on SiC |
| TLMB3106 | Blue, $I_V = (5.0 \text{ to } 20.0)$ mcd | GaN on SiC |

| ABSOLUTE MAXIMUM RATINGS ¹⁾ TLMB310. | | | | |
|---|--|------------|---------------|--------------------|
| PARAMETER | TEST CONDITION | SYMBOL | VALUE | UNIT |
| Reverse voltage | | V_R | 5 | V |
| DC Forward current | $T_{amb} \leq 60\text{ }^{\circ}\text{C}$ | I_F | 20 | mA |
| Surge forward current | $t_p \leq 10\text{ }\mu\text{s}$ | I_{FSM} | 0.1 | A |
| Power dissipation | $T_{amb} \leq 60\text{ }^{\circ}\text{C}$ | P_V | 100 | mW |
| Junction temperature | | T_j | 100 | $^{\circ}\text{C}$ |
| Operating temperature range | | T_{amb} | - 40 to + 100 | $^{\circ}\text{C}$ |
| Storage temperature range | | T_{stg} | - 40 to + 100 | $^{\circ}\text{C}$ |
| Soldering temperature | $t \leq 5\text{ s}$ | T_{sd} | 260 | $^{\circ}\text{C}$ |
| Thermal resistance junction/ambient | mounted on PC board (pad size > 16 mm ²) | R_{thJA} | 400 | K/W |

Note:

¹⁾ $T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

| OPTICAL AND ELECTRICAL CHARACTERISTICS ¹⁾ TLMB310., BLUE | | | | | | | |
|---|-------------------------------|----------|-------------|-----|----------|------|------|
| PARAMETER | TEST CONDITION | PART | SYMBOL | MIN | TYP. | MAX | UNIT |
| Luminous intensity ²⁾ | $I_F = 10\text{ mA}$ | TLMB3100 | I_V | 4.0 | 8.0 | | mcd |
| | | TLMB3101 | I_V | 4.0 | | 12.5 | mcd |
| | | TLMB3104 | I_V | 5.0 | | 12.5 | mcd |
| | | TLMB3106 | I_V | 5.0 | | 20.0 | mcd |
| Dominant wavelength | $I_F = 10\text{ mA}$ | | λ_d | | 466 | | nm |
| Peak wavelength | $I_F = 10\text{ mA}$ | | λ_p | | 428 | | nm |
| Angle of half intensity | $I_F = 10\text{ mA}$ | | φ | | ± 60 | | deg |
| Forward voltage | $I_F = 20\text{ mA}$ | | V_F | | 3.9 | 4.5 | V |
| Reverse voltage | $I_R = 10\text{ }\mu\text{A}$ | | V_R | 5 | | | V |

Note:

¹⁾ $T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

²⁾ In one packing unit $I_{Vmax}/I_{Vmin} \leq 1.6$

TYPICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified

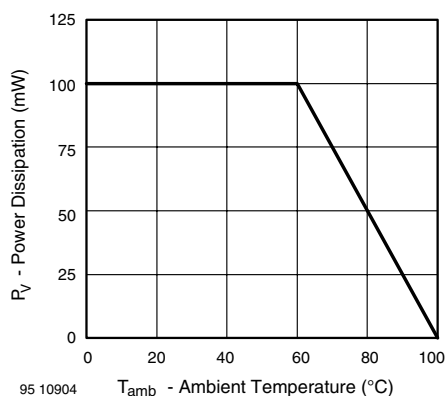


Figure 1. Power Dissipation vs. Ambient Temperature

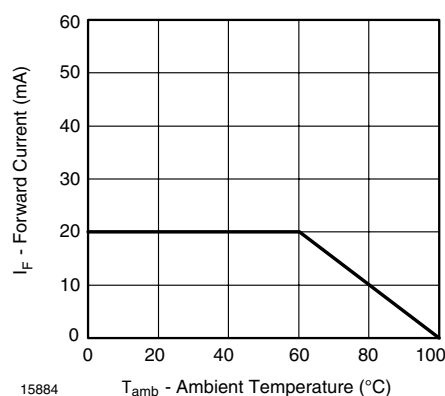


Figure 2. Forward Current vs. Ambient Temperature for InGaN

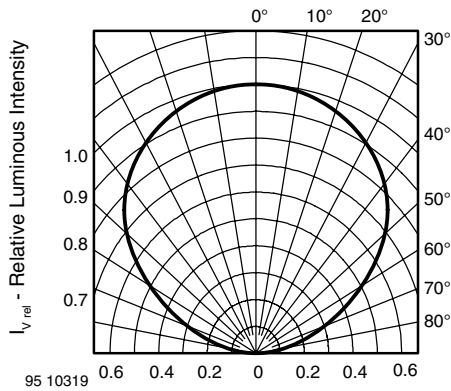


Figure 3. Rel. Luminous Intensity vs. Angular Displacement

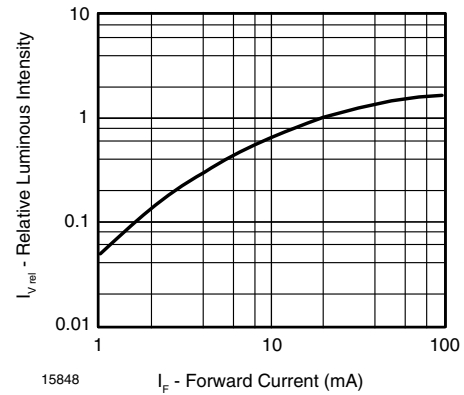


Figure 6. Relative Luminous Flux vs. Forward Current

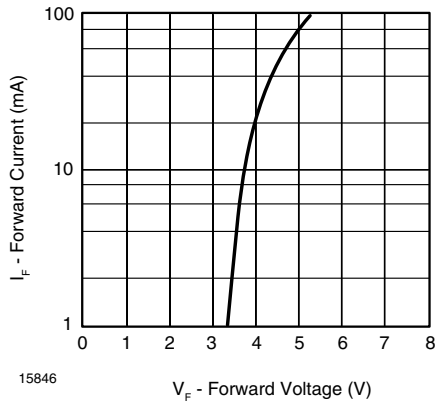


Figure 4. Forward Current vs. Forward Voltage

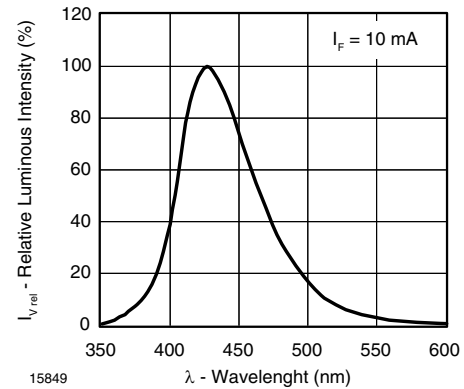


Figure 7. Relative Luminous Intensity vs. Wavelength

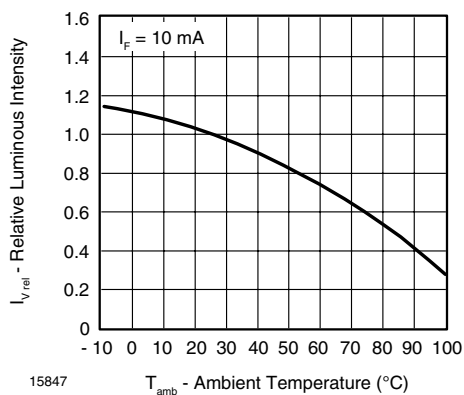


Figure 5. Rel. Luminous Flux vs. Ambient Temperature

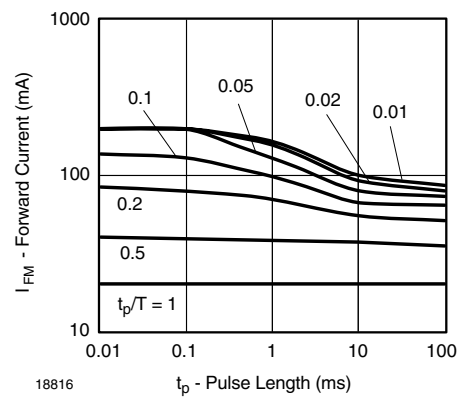
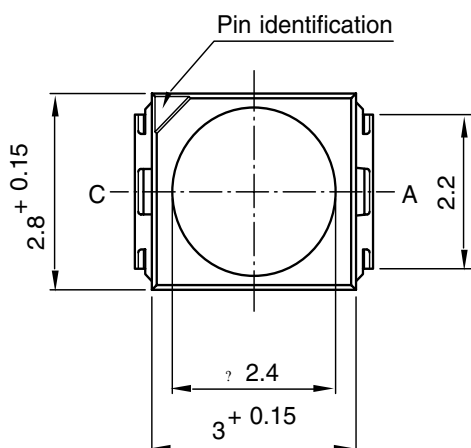
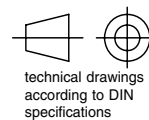
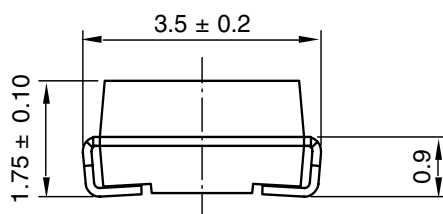
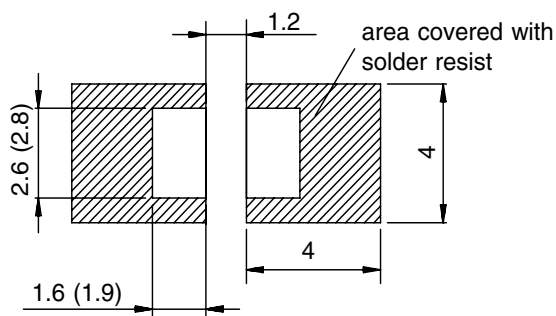


Figure 8. Forward Current vs. Pulse Length

PACKAGE DIMENSIONS in millimeters



Mounting Pad Layout



Drawing-No.: 6.541-5025.01-4

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**OZONE DEPLETING SUBSTANCES POLICY STATEMENT**

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design
and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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